DATA SHEET

NEC

SILICON POWER TRANSISTOR
2SA1647, 2SA1647-Z

PNP SILICON EPITAXIAL TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1647 is a mold power transistor developed for high-speed switching and features a very low collector-to-emitter saturation voltage.

This transistor is ideal for use in switching regulators, DC/DC converters, motor drivers, solenoid drivers, and other low-voltage power supply devices, as well as for high-current switching.

FEATURES

- Available for high-current control in small dimension
- Z type is a lead processed product and is deal for mounting a hybrid IC.
- Low collector saturation voltage:
  $V_{CE(sat)}$ = –0.3 V MAX. (@I_C = –3 A)
- Fast switching speed:
  t_f = 0.4 μs MAX. (@I_C = –3 A)
- High DC current gain and excellent linearity

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

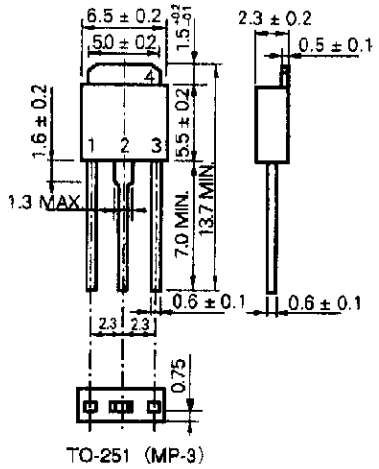
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–150	V
Collector to emitter voltage	V_{CEO}	–100	V
Base to emitter voltage	V_{EBO}	–7.0	V
Collector current (DC)	$I_{C(DC)}$	–5.0	A
Collector current (pulse)	$I_{C(pulse)}$*	–10	A
Base current (DC)	$I_{B(DC)}$	–2.5	A
Total power dissipation	P_T (T_C = 25 °C)	18	W
Total power dissipation	P_T (T_A = 25 °C)	1.0**, 2.0***	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	–55 to +150	°C

*: PW ≤ 10 ms, duty cycle ≤ 50%

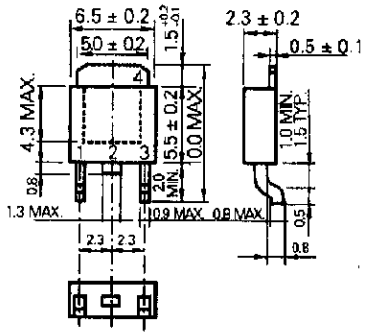
**: Printing board mounted

***: 7.5 mm^2 × 0.7 mm ceramic board mounted

PACKAGE DRAWING (UNIT: mm)



TO-251 (MP-3)



TO-252 (MP-3Z)

Electrode Connection
1. Base
2. Collector
3. Emitter

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Document No. D14839EJ2V0DS00 (2nd edition)
Date Published April 2002 N CP(K)
Printed in Japan

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

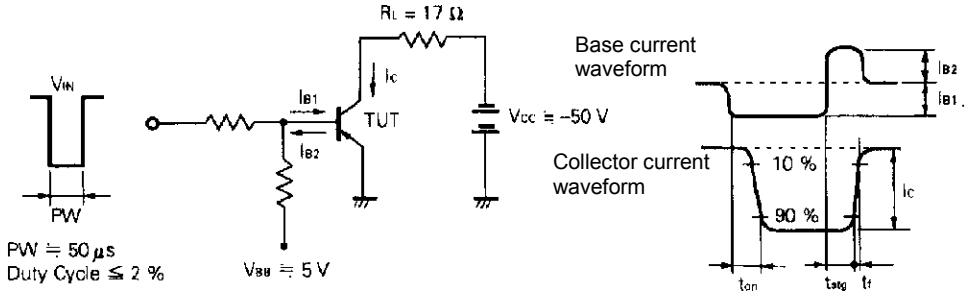
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector to emitter voltage	$V_{CEO(SUS)}$	I_C = –2.5 A, I_B = –0.25 A, L = 1 mH	–100			V
Collector to emitter voltage	$V_{CEX(SUS)}$	I_C = –2.5 A, I_{B1} = –I_{B2} = –0.25 A, $V_{BE(OFF)}$ = 1.5 V, L = 180 μH, clamped	–100			V
Collector cutoff current	I_{CBO}	V_{CB} = –100 V, I_E = 0			–10	μA
Collector cutoff current	I_{CER}	V_{CE} = –100 V, R_{BE} = 50 Ω, T_A = 125 °C			–1.0	mA
Collector cutoff current	I_{CEX1}	V_{CE} = –100 V, $V_{BE(OFF)}$ = 1.5 V			–10	μA
Collector cutoff current	I_{CEX2}	V_{CE} = –100 V, $V_{BE(OFF)}$ = 1.5 V, T_A = 125 °C			–1.0	mA
Emitter cutoff current	I_{EBO}	$V_{EB(OFF)}$ = –5.0 V, I_C = 0			–10	μA
DC current gain	h_{FE1}*	V_{CE} = –2.0 V, I_C = –0.5 A	100			
DC current gain	h_{FE2}*	V_{CE} = –2.0 V, I_C = –1.0 A	100		400	
DC current gain	h_{FE3}*	V_{CE} = –2.0 V, I_C = –3.0 A	60			
Collector saturation voltage	$V_{CE(sat)1}$*	I_C = –3.0 A, I_B = –0.15 A			–0.3	V
Collector saturation voltage	$V_{CE(sat)2}$*	I_C = –4.0 A, I_B = –0.2 A			–0.5	V
Base saturation voltage	$V_{BE(sat)1}$*	I_C = –3.0 A, I_B = –0.15 A			–1.2	V
Base saturation voltage	$V_{BE(sat)2}$*	I_C = –4.0 A, I_B = –0.2 A			–1.5	V
Collector capacitance	C_{ob}	V_{CB} = –10 V, I_E = 0, f = 1.0 MHz		110		pF
Gain bandwidth product	f_T	V_{CE} = –10 V, I_C = 0.5 A		90		MHz
Turn-on time	t_{on}	I_C = –3.0 A, R_L = 17 Ω, I_{B1} = –I_{B2} = –0.15 A, V_{CC} ≅ –50 V Refer to the test circuit.			0.3	μs
Storage time	t_{stg}				1.5	μs
Fall time	t_f				0.4	μs

* Pulse test PW ≤ 350 μs, duty cycle ≤ 2%/Pulsed

h_{FE} CLASSIFICATION

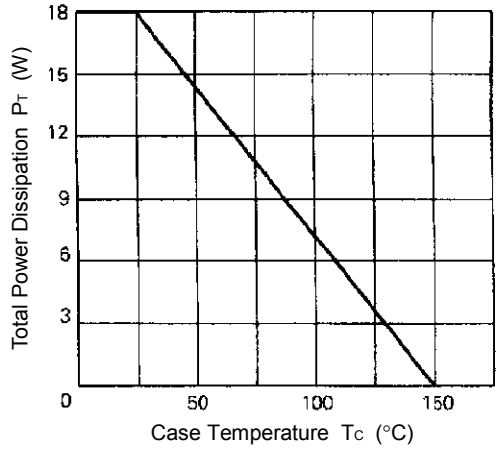
Marking	M	L	K
h_{FE2}	100 to 200	150 to 300	200 to 400

SWITCHING TIME TEST CIRCUIT

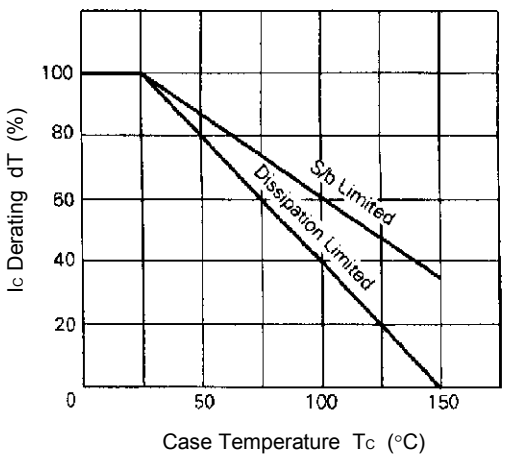


TYPICAL CHARACTERISTICS (T_A = 25°C)

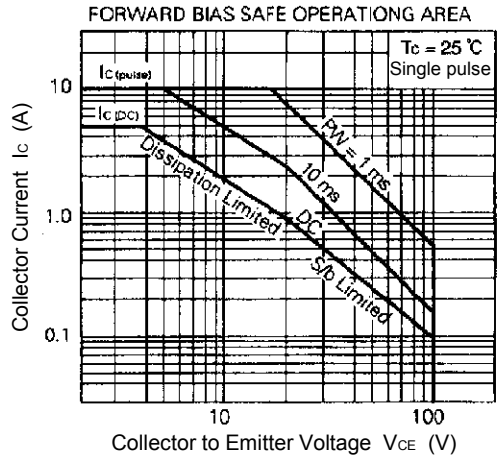
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



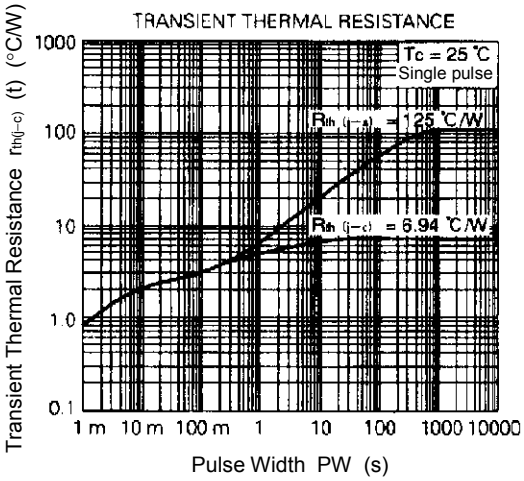
DERATING CURVE OF SAFE OPERATING AREA



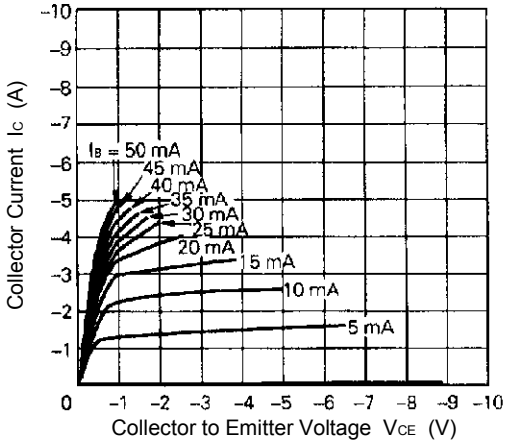
FORWARD BIAS SAFE OPERATIONG AREA



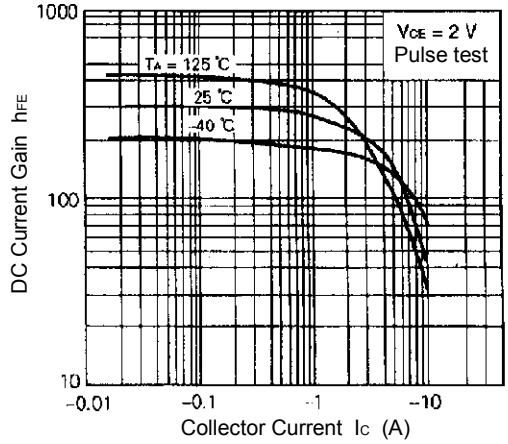
TRANSIENT THERMAL RESISTANCE



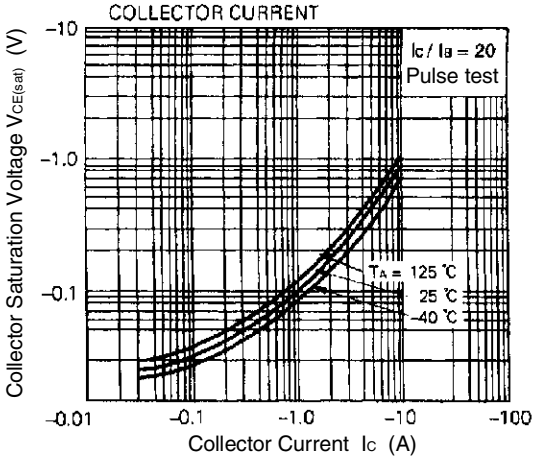
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



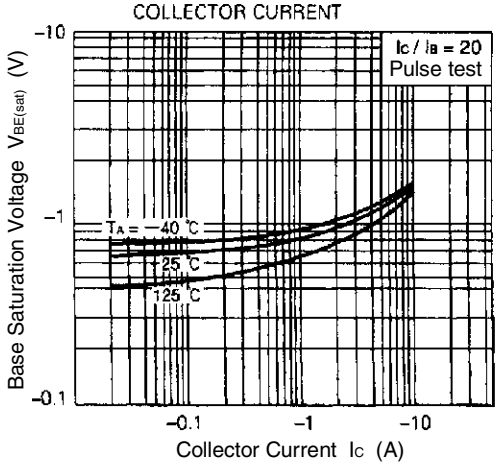
DC CURRENT GAIN vs. COLLECTOR CURRENT



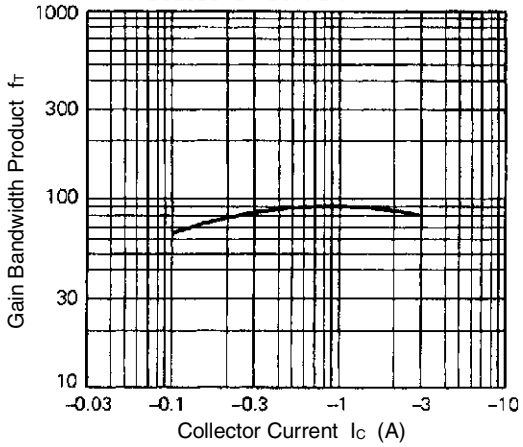
COLLECTOR SATURATION VOLTAGE vs. COLLECTOR CURRENT



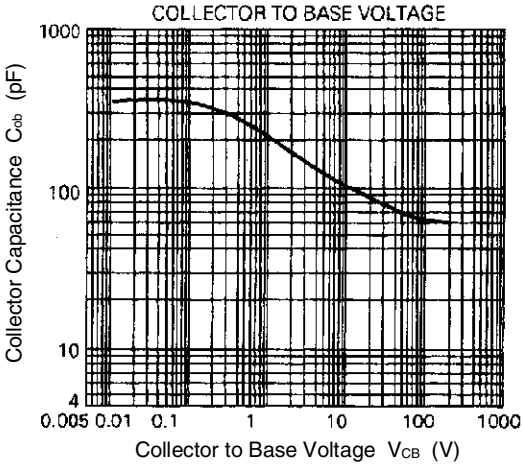
BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



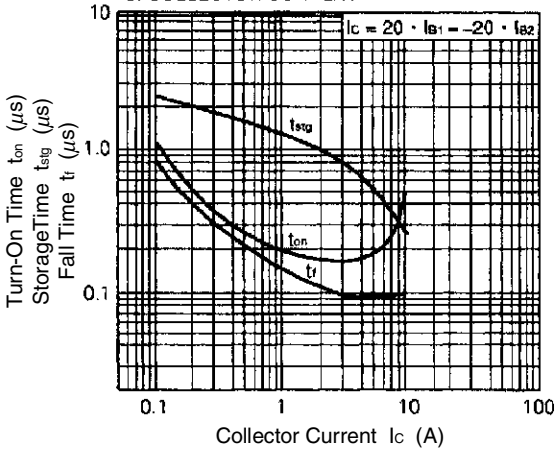
GAIN BANDWIDTH PRODUCT vs. COLLECTOR CURRENT



OUTPUT CAPACITANCE vs. COLLECTOR TO BASE VOLTAGE



TURN ON TIME, STORAGE TIME AND FALL TIME vs. COLLECTOR CURRENT



[MEMO]

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